Atty Docket No.: 200310982-1 App. Scr. No.: 10/660,297

IN THE CLAIMS:

Please find below a listing of all of the pending claims. The status of each claim is set forth in parentheses.

- 1. (Original) A data storage device comprising:
 - a probe tip mounted on a suspension mechanism;
 - a data storage layer;
- at least one conducting layer wherein a capacitance is formed between the suspension mechanism and the at least one conducting layer; and
- a sensor for sensing a change in the capacitance based on a displacement of the probe tip due to the presence of a bit.
- 2. (Original) The data storage device of claim 1 wherein the data storage layer is in contact with the probe tip.
- 3. (Original) The data storage device of claim 2 wherein the data storage layer includes the bit and the bit comprises at least one of a pit or a protrusion.
- 4. (Original) The data storage device of claim 1 wherein the data storage layer comprises a polymer material.
- 5. (Previously Presented) The data storage device of claim 1 wherein the at least one conducting layer comprises a conducting thin film.

Atty Docket No.: 200310982-1

App. Scr. No.: 10/660,297

6. (Previously Presented) The data storage device of claim 5 wherein the conducting thin film comprises at least one of a deposited metal film of Mo, Cu, TA, and an alloy.

7. (Previously Presented) The data storage device of claim 1 wherein the at least one conducting layer comprises a conducting substrate.

8. (Original) The data storage device of claim 7 wherein the conducting substrate comprises a doped silicon material.

9. (Original) The data storage device of claim 1 wherein the suspension mechanism includes a flexible cantilever.

10. (Original) The data storage device of claim 9 wherein the capacitance is formed on at least one side of the flexible cantilever.

- 11. (Original) The data storage device of claim 9 wherein a first capacitance is formed on a first side of the flexible cantilever and a second capacitance is formed on a second side of the flexible cantilever.
- 12. (Original) The data storage device of claim 11 wherein the change in capacitance comprises a difference in capacitance between the first capacitance and the second capacitance.

Atty Docket No.: 200310982-1 App. Scr. No.: 10/660,297

13. (Original) A method of reading data from a data storage device comprising: suspending a probe tip over a data storage layer via a suspension mechanism; providing at least one conducting layer wherein a capacitance is formed between the suspension mechanism and the at least one conducting layer; and

sensing a change in the capacitance based on a displacement of the probe tip due to the presence of a bit.

- 14. (Original) The method of claim 13 wherein the data storage layer comprises a polymer material.
- 15. (Original) The method of claim 13 wherein the at least one conducting layer comprises a conducting thin film.
- 16. (Previously Presented) The method of claim 15 wherein the conducting thin film comprises at least one of a deposited metal film of Mo, Cu, TA, and an alloy.
- 17. (Original) The method of claim 13 wherein the at least one conducting layer comprises a conducting substrate.
- 18. (Original) The method of claim 17 wherein the conducting substrate comprises a doped silicon material.

Atty Docket No.: 200310982-1

App. Scr. No.: 10/660,297

19. (Original) The method of claim 13 wherein the suspension mechanism further includes a flexible cantilever and the act of providing at least one conducting layer further comprises providing a conducting layer within the suspension mechanism whereby a capacitance is formed between the conducting layer and the flexible cantilever.

20. (Original) The method of claim 13 wherein the suspension mechanism further includes a flexible cantilever and the act of providing at least one conducting layer includes providing a first conducting layer on a first side of the flexible cantilever and a second conducting layer on a second side of the flexible cantilever wherein a first capacitance is formed on the first side of the flexible cantilever and a second capacitance is formed on the second side of the flexible cantilever.

- 21. (Original) The method of claim 20 wherein the act of sensing a change in capacitance comprises sensing a difference in capacitance between the first and second capacitance.
- 22. (Original) The method of claim 13 wherein the data storage layer includes the bit and the bit comprises at least one of a pit or protrusion.
- 23. (Original) A computer system comprising:
 - a central processing unit; and
 - a data storage device coupled to the central processing unit comprising:
 - a probe tip mounted on a suspension mechanism;
 - a data storage layer;

Atty Docket No.: 200310982-1 App. Scr. No.: 10/660,297

at least one conducting layer wherein a capacitance is formed between the suspension mechanism and the at least one conducting layer, and

a sensor for sensing a change in the capacitance based on a displacement of the probe tip due to the presence of a bit.

24. (Previously Presented) A data storage device comprising:

a probe tip mounted on a flexible suspension mechanism;

at least one capacitor coupled to the flexible suspension mechanism; and

a sensor for sensing a change in capacitance of the at least one capacitor based on a displacement of the probe tip due to the presence of a bit.